

A2, cont
portion by development.

A3
29. (Amended) The resist pattern according to Claim 24, wherein a width of the resist pattern is 1 μm or more.

30. (Amended) The resist pattern according to Claim 24, wherein a height of the resist pattern is 1 to 150 μm .

31. (Amended) The resist pattern laminated substrate which comprises the resist pattern according to Claim 24, wherein it is formed on a substrate for preparing a circuit.

A4
40. (Amended) The wiring pattern according to Claim 34, wherein a height of the wiring pattern is 0.01 to 200 μm .
